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TITLE: SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

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INVENTOR-INFORMATION:

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ABSTRACT:

**PURPOSE:** To remove a failure due to a base oxide film when ionizing radiation comes and to allow contaminant substance reemitted from gettering nuclei to reach the vicinity of an element.

**CONSTITUTION:** Voids 10 in contact with a joined semiconductor layer 3 are partly formed on an insulating layers 2, or the joined layer 3 is formed of a denuded zone in an element forming region. A semiconductor substrate has gettering nuclei at an insulating layer side, and voids are partly formed on the insulating layer of the semiconductor layer side.

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